

Exhibit A

Version of Amended Claims Showing Changes Made

25. (Amended) A nonvolatile memory array, comprising:
- a monolithic three dimensional array of nonvolatile memory devices comprising an array of EEPROMs;
 - at least one driver circuit;
 - a substrate;
 - a first plurality of spaced-apart conductors disposed at a first height above the substrate in a first direction; and
 - a second plurality of spaced-apart rail-stacks disposed above the first height in a second direction different from the first direction, each rail-stack including a semiconductor film of a first conductivity type in contact with said first plurality of spaced-apart conductors, a local charge storage film disposed above the semiconductor film and a conductive film disposed above the local charge storage film,
- wherein the at least one driver circuit is not located in a bulk monocrystalline silicon substrate.